February 1995

LM709 Operational Amplifier

General Description

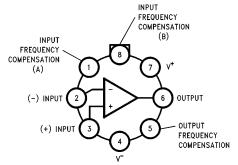
The LM709 series is a monolithic operational amplifier intended for general-purpose applications. Operation is completely specified over the range of voltages commonly used for these devices. The design, in addition to providing high gain, minimizes both offset voltage and bias currents. Further, the class-B output stage gives a large output capability with minimum power drain.

External components are used to frequency compensate the amplifier. Although the unity-gain compensation network specified will make the amplifier unconditionally stable in all feedback configurations, compensation can be tailored to optimize high-frequency performance for any gain setting.

The LM709C is the commercial-industrial version of the LM709. It is identical to the LM709 except that it is specified for operation from 0°C to \pm 70°C.

Connection Diagrams

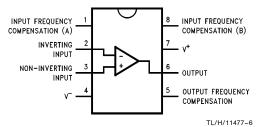
Metal Can Package



TL/H/11477-4

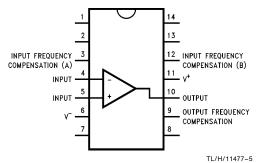
Order Number LM709AH, LM709H or LM709CH See NS Package Number H08C

Dual-In-Line Package



Order Number LM709CN-8 See NS Package Number N08E

Dual-In-Line Package



Order Number LM709CN See NS Package Number N14A

Absolute Maximum Ratings (Note 3)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage

LM709/LM709A/LM709C $\pm\,18V$

Power Dissipation (Note 1)

300 mW LM709/LM709A LM709C 250 mW

Differential Input Voltage

LM709/LM709A/LM709C $\pm\,5V$

Input Voltage

LM709/LM709A/LM709C $\pm\,10V$

Output Short-Circuit Duration ($T_A = +25^{\circ}C$)

LM709/LM709A/LM709C 5 seconds Storage Temperature Range LM709/LM709A/LM709C

-65°C to +150°C

Lead Temperature (Soldering, 10 sec.) LM709/LM709A/LM709C

300°C

Operating Ratings (Note 3)

Junction Temperature Range (Note 1)

LM709/LM709A -55°C to +150°C

LM709C 0°C to $\,\pm\,100^{\circ}\text{C}$

Thermal Resistance (θ_{JA})

150°C/W, (θ_{JC}) 45°C/W H Package 8-Pin N Package 134°C/W 109°C/W

14-Pin N Package

Electrical Characteristics (Note 2)

Parameter	Conditions	LM709A			LM709			LM709C			Units
		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Jillis
Input Offset Voltage	$T_{A}=$ 25°C, $R_{S}\leq$ 10 k Ω		0.6	2.0		1.0	5.0		2.0	7.5	mV
Input Bias Current	$T_A = 25^{\circ}C$		100	200		200	500		300	1500	nA
Input Offset Current	$T_A = 25^{\circ}C$		10	50		50	200		100	500	nA
Input Resistance	$T_A = 25^{\circ}C$	350	700		150	400		50	250		kΩ
Output Resistance	$T_A = 25^{\circ}C$		150			150			150		Ω
Supply Current	$T_A = 25^{\circ}C, V_S = \pm 15V$		2.5	3.6		2.6	5.5		2.6	6.6	mA
Transient Response Risetime Overshoot	$V_{IN} = 20$ mV, $C_L \le 100$ pF $T_A = 25^{\circ}C$			1.5 30		0.3 10	1.0 30		0.3 10	1.0 30	μs %
Slew Rate	$T_A = 25^{\circ}C$		0.25			0.25			0.25		V/μs
Input Offset Voltage	$R_S \le 10 k\Omega$			3.0			6.0			10	mV
Average Temperature Coefficient of Input Offset Voltage	$\begin{split} R_S = 50\Omega & T_A = 25^\circ\text{C to }T_{\text{MAX}} \\ T_A = 25^\circ\text{C to }T_{\text{MIN}} \\ R_S = 10 \text{ k}\Omega & T_A = 25^\circ\text{C to }T_{\text{MAX}} \\ T_A = 25^\circ\text{C to }T_{\text{MIN}} \end{split}$		1.8 1.8 2.0 4.8	10 10 15 25		3.0 6.0			6.0 12		μV/°C
Large Signal Voltage Gain	$V_S = \pm 15 V, R_L \ge 2 k\Omega$ $V_{OUT} = \pm 10 V$	25		70	25	45	70	15	45		V/mV
Output Voltage Swing	$\begin{split} V_S = \pm 15 V, R_L = 10 k\Omega \\ V_S = \pm 15 V, R_L = 2 k\Omega \end{split}$	±12 ±10			±12 ±10	±14 ±13		±12 ±10	±14 ±13		V
Input Voltage Range	$V_S = \pm 15V$	±8			±8	±10		±8	±10		V
Common-Mode Rejection Ratio	$R_S \le 10 \text{ k}\Omega$	80	110		70	90		65	90		dB
Supply Voltage Rejection Ratio	$R_S \le 10 \text{ k}\Omega$		40	100		25	150		25	200	μV/V
Input Offset Current	$\begin{aligned} T_{A} &= T_{MAX} \\ T_{A} &= T_{MIN} \end{aligned}$		3.5 40	50 250		20 100	200 500		75 125	400 750	nA
Input Bias Current	$T_A = T_{MIN}$		0.3	0.6		0.5	1.5		0.36	2.0	μΑ
Input Resistance	$T_A = T_{MIN}$	85	170		40	100		50	250		kΩ

Note 1: For operating at elevated temperatures, the device must be derated based on a 150°C maximum junction temperature for LM709/LM709A and 100°C maximum for L709C. For operating at elevated temperatures, the device must be derated based on thermal resistance θ_{JA} , $T_{J(MAX)}$ and T_{A} .

Note 2: These specifications apply for $-55^{\circ}\text{C} \le T_{A} \le +125^{\circ}\text{C}$ for the LM709/LM709A and $0^{\circ}\text{C} \le T_{A} \le +70^{\circ}\text{C}$ for the LM709C with the following conditions: $\pm 9V \le V_{S} \le \pm 15V$, C1 = 5000 pF, R1 = 1.5 k Ω , C2 = 200 pF and R2 = 51 Ω .

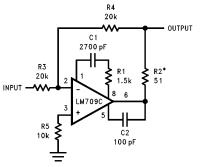
Note 3: Absolute Maximum Ratings indicate limits which if exceeded may result in damage. Operating Ratings are conditions where the device is expected to be functional but not necessarily within the guaranteed performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics.

Q10

R11 2.4k

Typical Applications**

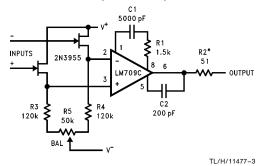
Unity Gain Inverting Amplifier



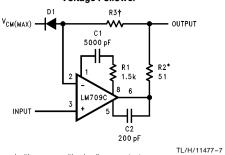
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FET Operational Amplifier

TL/H/11477-1

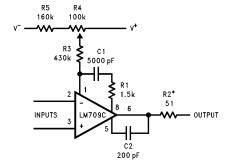


Voltage Follower



 $\ensuremath{^{*}\text{To}}$ be used with any capacitive loading on output.

**Pin connections shown are for metal can package. †Should be equal to DC source resistance on input.

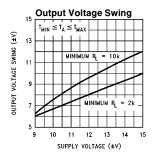


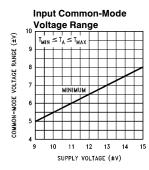
Offset Balancing Circuit

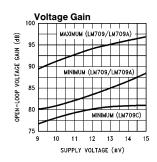
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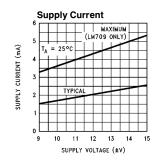
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Guaranteed Performance Characteristics



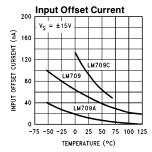


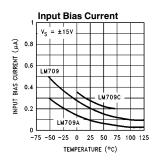


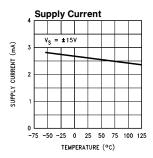


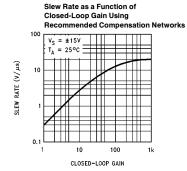
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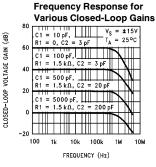
Typical Performance Characteristics

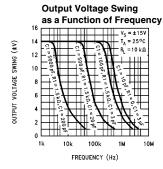


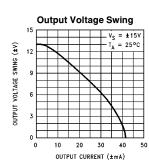


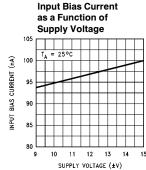




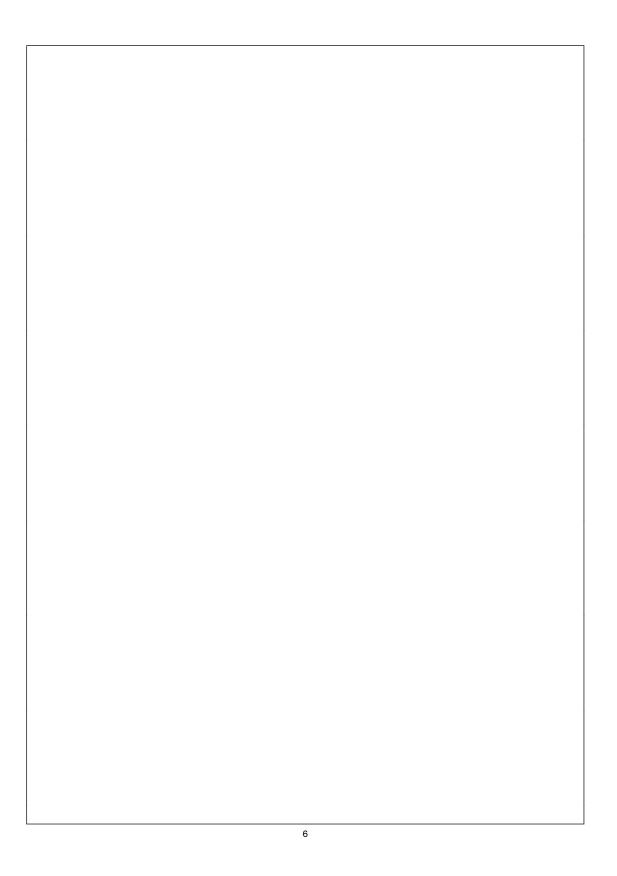


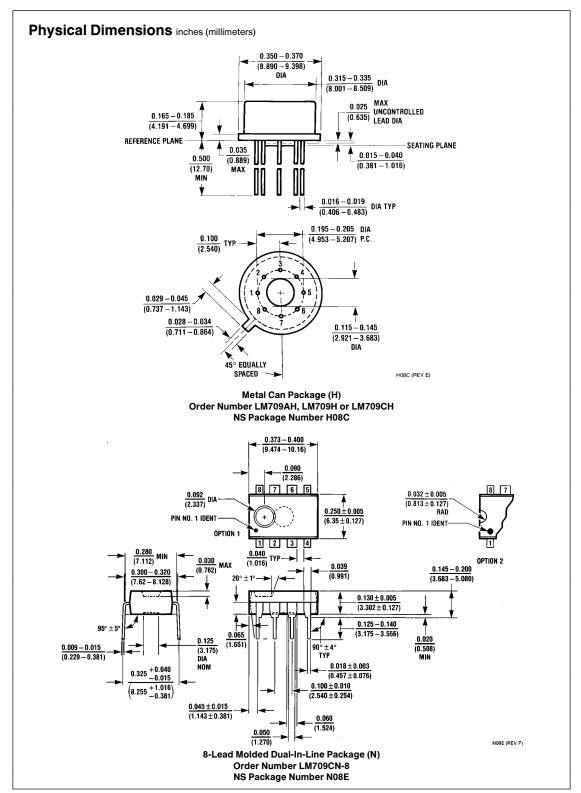




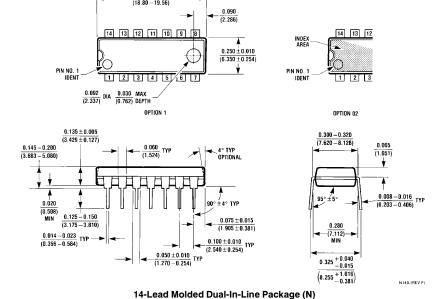


TL/H/11477-10





Physical Dimensions inches (millimeters) (Continued)



Order Number LM709CN NS Package Number N14A

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